

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- Very fast switching
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- AEC-Q101 qualified

3. Applications

- DC to DC conversion
- High-speed line driver
- High-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{sp} = 25 °C		-	-	-6.7	А
P _{tot}	total power dissipation	T _{sp} = 25 °C		-	-	7.5	W
Static chara	acteristics	·	·				
R _{DSon}	drain-source on-state resistance	V _{GS} = -4.5 V; I _D = -3.4 A; T _j = 25 °C		-	88	110	mΩ



5. Pinning information

Table 2	Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	D	drain		D				
2	D	drain						
3	G	gate	2					
4	S	source	3 8 4					
5	D	drain	Transparent top view					
6	D	drain	DFN2020MD-6 (SOT1220)	s				
7	D	drain		017aaa259				
8	S	source						

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BUK4D110-20P		plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1220				

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK4D110-20P	6N

20 V, P-channel Trench MOSFET

8. Limiting values

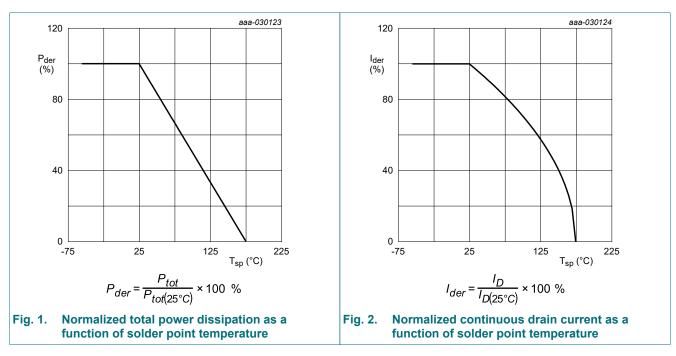
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

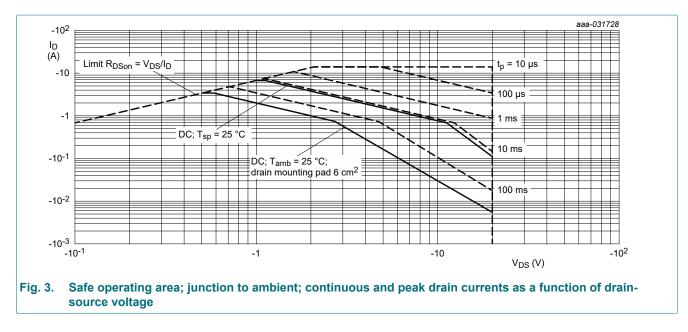
Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-12	12	V
ID	drain current	V _{GS} = -4.5 V; T _{sp} = 25 °C		-	-6.7	А
		V _{GS} = -4.5 V; T _{sp} = 100 °C		-	-4.2	A
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-3.4	А
I _{DM}	peak drain current	T_{sp} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-27	А
P _{tot}	total power dissipation	T _{sp} = 25 °C		-	7.5	W
		T _{amb} = 25 °C	[1]	-	2	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain	diode					
Is	source current	T _{sp} = 25 °C		-	-6.7	А
		T _{amb} = 25 °C	[1]	-	-1.9	А
I _{SM}	peak source current	single pulse; $t_p \le 10 \ \mu s$; $T_{sp} = 25 \ ^{\circ}C$		-	-27	A
ESD maximu	m rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	1000	V
Avalanche ru	iggedness		·			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ T_{j(init)} = 25 \text{ °C; } I_D = -0.5 \text{ A; DUT in}$ (avalanche (unclamped)		-	5	mJ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

[2] Measured between all pins.



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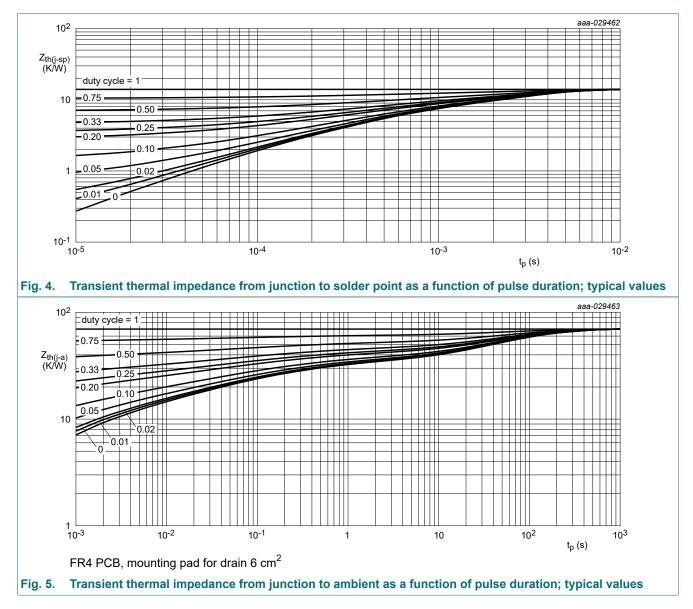


BUK4D110-20P

9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	66	76	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

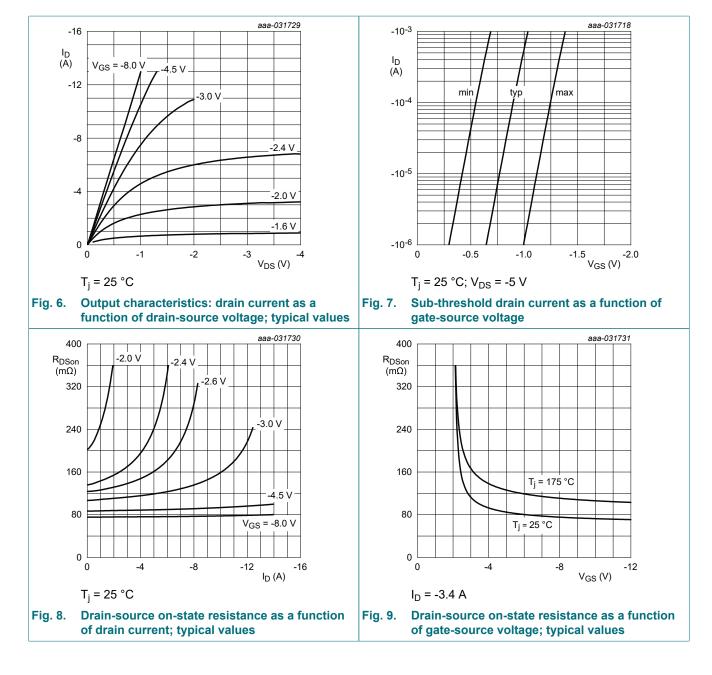
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



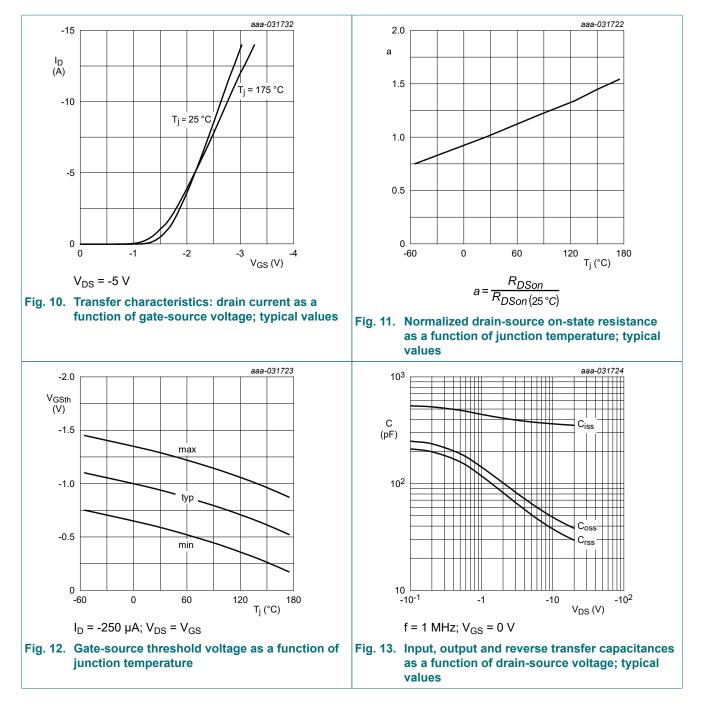
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	1				
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.6	-0.95	-1.3	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 125 °C	-	-	-20	μA
I _{GSS}	gate leakage current	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
R _{DSon}	drain-source on-state resistance	V _{GS} = -8 V; I _D = -3.4 A; T _j = 25 °C	-	75	96	mΩ
		V _{GS} = -8 V; I _D = -3.4 A; T _j = 175 °C	-	116	148	mΩ
		V _{GS} = -4.5 V; I _D = -3.4 A; T _j = 25 °C	-	88	110	mΩ
		V _{GS} = -2.5 V; I _D = -1 A; T _j = 25 °C	-	138	189	mΩ
9fs	forward transconductance	V_{DS} = -10 V; I _D = -3.4 A; T _j = 25 °C	-	6	-	S
R _G	gate resistance	f = 1 MHz	-	36	-	Ω
Dynamic ch	naracteristics		I			
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I _D = -3.2 A; V _{GS} = -4.5 V;	-	3.6	5	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.8	-	nC
Q _{GD}	gate-drain charge		-	1.2	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	365	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	49	-	pF
C _{rss}	reverse transfer capacitance	_	-	39	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I _D = -3.2 A; V _{GS} = -4.5 V;	-	4	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	7	-	ns
t _{d(off)}	turn-off delay time		-	9	-	ns
t _f	fall time		-	7	-	ns
Source-drai	in diode		1			
V _{SD}	source-drain voltage	I _S = -2 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.9	-1.2	V
t _{rr}	reverse recovery time	$I_{S} = -2 \text{ A}; \text{ d}I_{S}/\text{d}t = 100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	9	-	ns
Q _r	recovered charge	V _{DS} = -10 V; T _j = 25 °C	-	2	_	nC

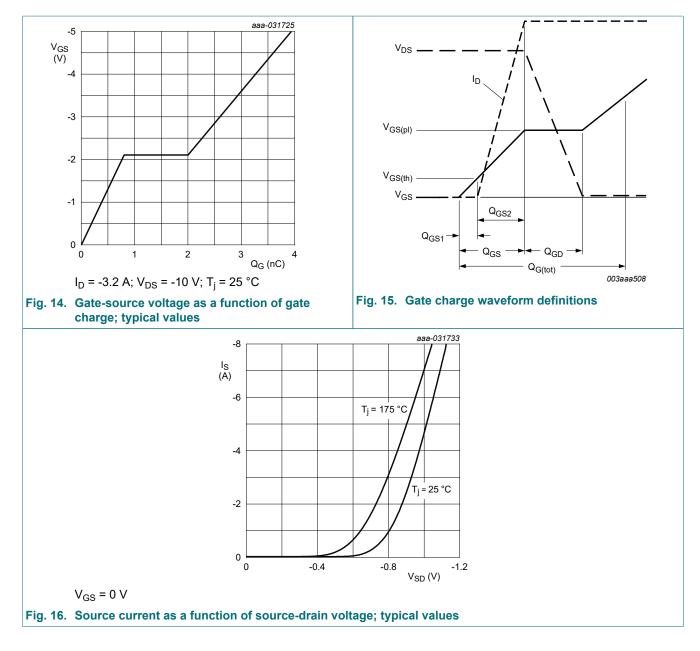
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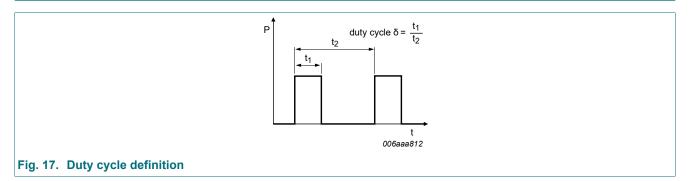
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11. Test information

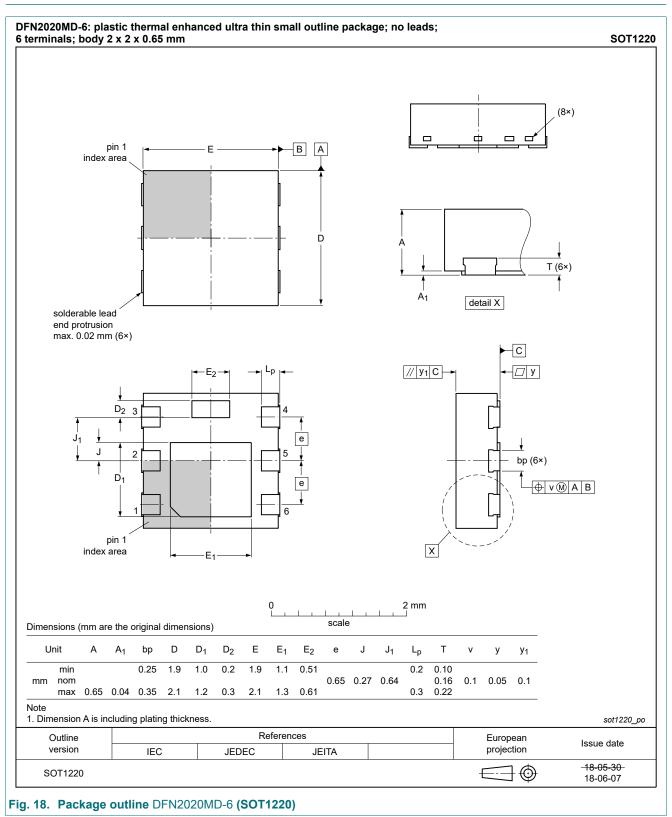


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

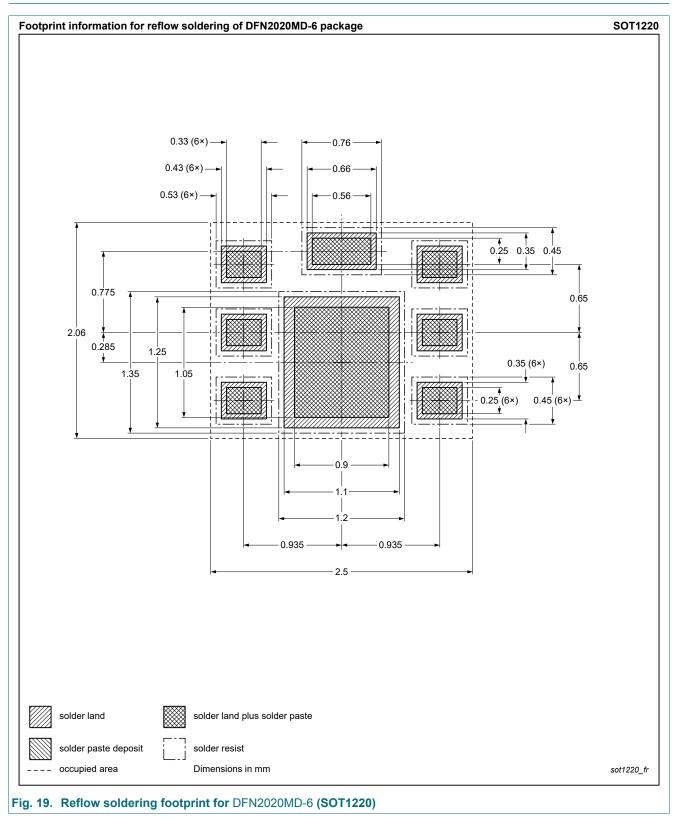
BUK4D110-20P

12. Package outline



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13. Soldering



14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BUK4D110-20P v.1	20200707	Product data sheet	-	-			

BUK4D110-20P

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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